

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (canceled).
2. (previously presented): The magnetic recording medium according to claim 16, wherein the conductive layer is disposed between the inorganic nonmagnetic substrate and the magnetic layer.
3. (previously presented): The magnetic recording medium according to claim 16, wherein the conductive layer is disposed on the inorganic nonmagnetic substrate on a side opposite to the magnetic layer.
4. (previously presented): The magnetic recording medium according to claim 16, wherein the conductive layer is disposed on an edge of the inorganic nonmagnetic substrate.
5. (previously presented): The magnetic recording medium according to claim 18, wherein the conductive layer contains a conductive metal oxide.

6. (previously presented): The magnetic recording medium according to claim 5, wherein the conductive metal oxide is selected from ZnO, Al₂O₃, In₂O₃, SiO₂, MgO, BaO, MoO₃, V₂O₅ and complex oxides thereof.

7. (previously presented): The magnetic recording medium according to claim 5, wherein the conductive metal oxide has a volume resistivity of not more than $10^7 \Omega\text{cm}$.

8. (canceled).

9. (previously presented): The magnetic recording medium according to claim 8, wherein the carbon black has an SBET of 50 to 500 m²/g.

10. (canceled).

11. (canceled).

12. (canceled).

13. (previously presented): The magnetic recording medium according to claim 16, wherein the magnetic recording medium has a surface electric resistance of not more than $10^{10} \Omega/\text{sq}$.

14. (previously presented): The magnetic recording medium according to claim 16 further comprising another magnetic layer, a nonmagnetic layer, or a back layer on a side opposite to the magnetic layer.

15. (previously presented): The magnetic recording medium according to claim 16 further comprising a protection film on the magnetic layer.

16. (previously presented): A magnetic recording medium comprising a magnetic layer on at least one side of an inorganic nonmagnetic substrate, the magnetic layer containing magnetic particles of a CuAu-type or Cu₃Au-type ferromagnetic ordered phase produced by a liquid phase method, wherein a conductive layer containing polyvinylbenzene sulfonate, polyvinyl benzyl trimethyl ammonium chloride, or a quaternary salt polymer is provided on at least one side of the inorganic nonmagnetic substrate, the conductive layer having a thickness of 10 to 400 nm.

17. (previously presented): The magnetic recording medium according to claim 16, wherein the thickness of the conductive layer is 20 to 400 nm.

18. (currently amended): A magnetic recording medium comprising a magnetic layer on at least one side of an inorganic nonmagnetic substrate, the magnetic layer containing magnetic particles of a CuAu-type or Cu₃Au-type ferromagnetic ordered phase produced by a liquid phase

method, wherein a conductive layer containing a conductive metal oxide or ~~carbon black~~ is provided on at least one side of the inorganic nonmagnetic substrate, the conductive layer having a thickness of 10 to 400 nm.

19. (previously presented): The magnetic recording medium according to claim 18, wherein the conductive layer is disposed on an edge of the inorganic nonmagnetic substrate.

20. (previously presented): The magnetic recording medium according to claim 16, wherein the CuAu-type or Cu₃Au-type ferromagnetic ordered phase produced by a liquid phase method is selected from FeNi, FePd, FePt, CoPt, CoAu, Ni₃Fe, FePd₃, Fe₃Pt, FePt₃, CoPt₃, Ni₃Pt, CrPt₃ and Ni₃Mn.

21. (previously presented): The magnetic recording medium according to claim 18, wherein the CuAu-type or Cu₃Au-type ferromagnetic ordered phase produced by a liquid phase method is selected from FeNi, FePd, FePt, CoPt, CoAu, Ni₃Fe, FePd₃, Fe₃Pt, FePt₃, CoPt₃, Ni₃Pt, CrPt₃ and Ni₃Mn.

22. (previously presented): The magnetic recording medium according to claim 6, wherein the CuAu-type or Cu₃Au-type ferromagnetic ordered phase produced by a liquid phase method is selected from FeNi, FePd, FePt, CoPt, CoAu, Ni₃Fe, FePd₃, Fe₃Pt, FePt₃, CoPt₃, Ni₃Pt, CrPt₃ and Ni₃Mn.